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INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	10/728,436
(Use as many sheets as necessary)	Filing Date	December 5, 2003
010	First Named Inventor	Chen, Yung-Tin
/015	Group Art Unit	1756
MAY 2 1 20	xaminer Name	Unknown
Sheet 1 of 3	torney Docket No: N	MA-111
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Exami Initial		Cite No '	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	Tr
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	Group Art Unit	1756	
	Examiner Name	Unknown	
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